

Abstract

A semiconductor device and a production method therefor are provided. In a semiconductor device (1), a contact (C5a) extends over a first select gate electrode (G2a) from a top portion of a contact installation structure (10a) having a configuration same as that of a memory gate structure (4a). The semiconductor device (1) includes no mounting portion (102b) on a top portion of a memory gate structure (110) unlike a conventional case (FIG. 13). Accordingly, the distance to an upper wiring layer can be reduced to achieve a reduced aspect ratio and hence increase in a contact resistance value is avoided. In addition, the contact installation structure (10a) can be further spaced from the upper wiring layer to avoid contact failure with the upper wiring layer.